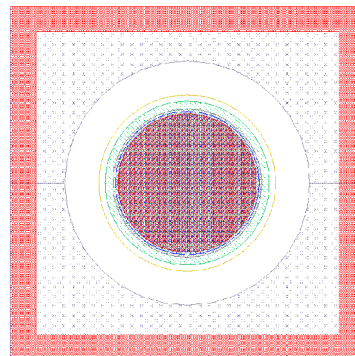


## 2KG028075JL SWITCHING DIODE CHIPS

### DESCRIPTION

- 2KG028075JL is a high speed switching diode chip fabricated in planar technology.
- This chip can be encapsulated as 1N4148 switching diode.
- This chip has several thicknesses, can suit for different plastic package. The top electrodes material is Al, and the back-side electrodes material is Au.
- Chip size: 0.28 X 0.28 (mm<sup>2</sup>).



2KG028XXX CHIP TOPOGRAPHY

### 2KG028075JL ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C)

| Characteristics       | Symbol          | Test Conditions                                                                                                       | Min. | Typ. | Max. | Unit |
|-----------------------|-----------------|-----------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| Forward Voltage       | V <sub>F</sub>  | I <sub>F</sub> =10mA.                                                                                                 | --   | --   | 1.0  | V    |
|                       |                 | I <sub>F</sub> =100mA.                                                                                                | 0.62 | 0.9  | 1.2  | V    |
| Reverse voltage       | V <sub>BR</sub> | I <sub>B</sub> =100μA.                                                                                                | 100  | 120  | --   | V    |
| Reverse Current       | I <sub>R</sub>  | V <sub>R</sub> =20V.                                                                                                  | --   | --   | 25   | nA   |
|                       |                 | V <sub>R</sub> =75V.                                                                                                  | --   | --   | 5    | μA   |
| Diode Capacitance     | C <sub>d</sub>  | f=1MHz; V <sub>R</sub> =0.                                                                                            | --   | 1.9  | 4    | pF   |
| Reverse Recovery Time | t <sub>rr</sub> | When switched from I <sub>F</sub> =10mA to V <sub>R</sub> =6V; R <sub>L</sub> =100Ω; measured at I <sub>R</sub> =1mA. | --   | --   | 4    | ns   |